

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3439889	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 18:02
L2	196394	1 and (nonvolatile or non-volatile)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 18:02
L3	1	2 and cell with transistor with parallel\$5 with silicid\$5 adj polysilic\$5 near3 fuse near3 resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 18:04
L4	1	2 and cell with transistor with parallel\$5 with fuse near3 resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 18:04
L5	45	2 and cell with transistor with parallel\$5 with resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 18:05
L6	1	2 and cell with transistor with parallel\$5 with resistor with polysilic\$5 with fuse	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 18:05

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L1	3	((memory or storage) and cell and transistor and parallel and silicid\$5 and polysilic\$5 and fuse near3 resistor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/14 18:26